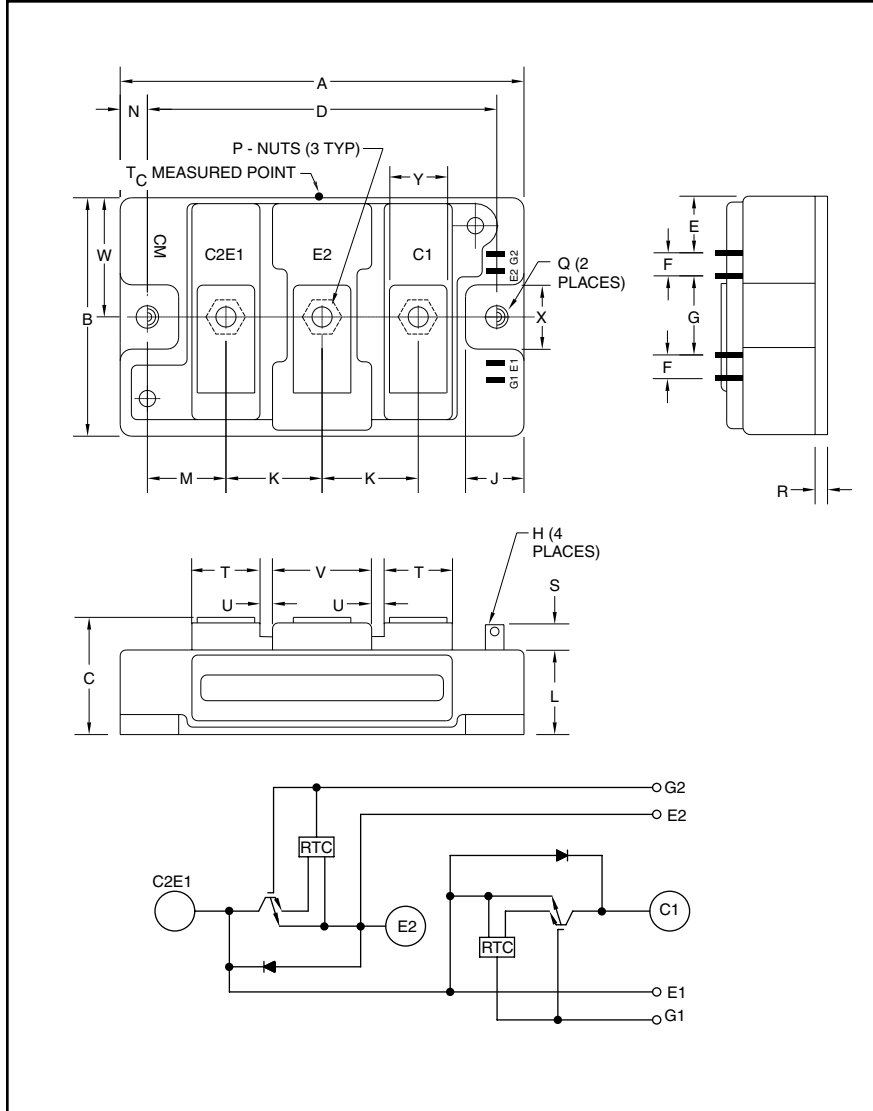


### Trench Gate Design Dual IGBTMOD™ 75 Amperes/600 Volts



Outline Drawing and Circuit Diagram

Dimensions	Inches	Millimeters
A	3.70	94.0
B	1.89	48.0
C	1.18 +0.04/-0.02	30.0 +1.0/-0.5
D	3.15±0.01	80.0±0.25
E	0.43	11.0
F	0.16	4.0
G	0.71	18.0
H	0.02	0.5
J	0.53	13.5
K	0.91	23.0
L	0.83	21.2
M	0.67	17.0

Dimensions	Inches	Millimeters
N	0.28	7.0
P	M5	M5
Q	Dia. 0.26	6.5 Dia.
R	0.02	4.0
S	0.30	7.5
T	0.63	16.0
U	0.10	2.5
V	1.0	25.0
W	0.94	24.0
X	0.51	13.0
Y	0.47	12.0
Z	0.47	12.0



#### Description:

Powerex IGBTMOD™ Modules are designed for use in switching applications. Each module consists of two IGBT Transistors in a half-bridge configuration with each transistor having a reverse-connected super-fast recovery free-wheel diode. All components and interconnects are isolated from the heat sinking baseplate, offering simplified system assembly and thermal management.

#### Features:

- Low Drive Power
- Low  $V_{CE(sat)}$
- Discrete Super-Fast Recovery Free-Wheel Diode
- Isolated Baseplate for Easy Heat Sinking

#### Applications:

- AC Motor Control
- UPS
- Battery Powered Supplies

#### Ordering Information:

Example: Select the complete module number you desire from the table - i.e. CM75DU-12F is a 600V ( $V_{CES}$ ), 75 Ampere Dual IGBTMOD™ Power Module.

Type	Current Rating Amperes	$V_{CES}$ Volts (x 50)
CM	75	12

**CM75DU-12F**  
**Trench Gate Design Dual IGBTMOD™**  
 75 Amperes/600 Volts

**Absolute Maximum Ratings,  $T_j = 25^\circ\text{C}$  unless otherwise specified**

Ratings	Symbol	CM75DU-12F	Units
Junction Temperature	$T_j$	-40 to 150	$^\circ\text{C}$
Storage Temperature	$T_{\text{stg}}$	-40 to 125	$^\circ\text{C}$
Collector-Emitter Voltage (G-E SHORT)	$V_{\text{CES}}$	600	Volts
Gate-Emitter Voltage (C-E SHORT)	$V_{\text{GES}}$	$\pm 20$	Volts
Collector Current ( $T_c = 25^\circ\text{C}$ )	$I_C$	75	Amperes
Peak Collector Current	$I_{\text{CM}}$	150*	Amperes
Emitter Current** ( $T_c = 25^\circ\text{C}$ )	$I_E$	75	Amperes
Peak Emitter Current**	$I_{\text{EM}}$	150*	Amperes
Maximum Collector Dissipation ( $T_c = 25^\circ\text{C}$ , $T_j \leq 150^\circ\text{C}$ )	$P_c$	290	Watts
Mounting Torque, M5 Main Terminal	–	40	in-lb
Mounting Torque, M5 Mounting	–	40	in-lb
Weight	–	310	Grams
Isolation Voltage (Main Terminal to Baseplate, AC 1 min.)	$V_{\text{iso}}$	2500	Volts

**Static Electrical Characteristics,  $T_j = 25^\circ\text{C}$  unless otherwise specified**

Characteristics	Symbol	Test Conditions	Min.	Typ.	Max.	Units
Collector-Cutoff Current	$I_{\text{CES}}$	$V_{\text{CE}} = V_{\text{CES}}$ , $V_{\text{GE}} = 0\text{V}$	–	–	1	mA
Gate Leakage Current	$I_{\text{GES}}$	$V_{\text{GE}} = V_{\text{GES}}$ , $V_{\text{CE}} = 0\text{V}$	–	–	20	$\mu\text{A}$
Gate-Emitter Threshold Voltage	$V_{\text{GE(th)}}$	$I_C = 7.5\text{mA}$ , $V_{\text{CE}} = 10\text{V}$	5	6	7	Volts
Collector-Emitter Saturation Voltage	$V_{\text{CE(sat)}}$	$I_C = 75\text{A}$ , $V_{\text{GE}} = 15\text{V}$ , $T_j = 25^\circ\text{C}$	–	1.6	2.2	Volts
		$I_C = 75\text{A}$ , $V_{\text{GE}} = 15\text{V}$ , $T_j = 125^\circ\text{C}$	–	1.6	–	Volts
Total Gate Charge	$Q_G$	$V_{\text{CC}} = 300\text{V}$ , $I_C = 75\text{A}$ , $V_{\text{GE}} = 15\text{V}$	–	465	–	nC
Emitter-Collector Voltage**	$V_{\text{EC}}$	$I_E = 75\text{A}$ , $V_{\text{GE}} = 0\text{V}$	–	–	2.6	Volts

\* Pulse width and repetition rate should be such that the device junction temperature ( $T_j$ ) does not exceed  $T_{j(\text{max})}$  rating.

\*\* Represents characteristics of the anti-parallel, emitter-to-collector free-wheel diode (FWDI).

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### Dynamic Electrical Characteristics, $T_j = 25^\circ\text{C}$ unless otherwise specified

Characteristics	Symbol	Test Conditions	Min.	Typ.	Max.	Units
Input Capacitance	$C_{ies}$		–	–	20	nf
Output Capacitance	$C_{oes}$	$V_{CE} = 10V, V_{GE} = 0V$	–	–	1.4	nf
Reverse Transfer Capacitance	$C_{res}$		–	–	0.75	nf
Inductive	Turn-on Delay Time	$V_{CC} = 300V, I_C = 75A,$ $V_{GE1} = V_{GE2} = 15V,$ $R_G = 8.3\Omega,$	–	–	100	ns
Load	Rise Time					
Switch	Turn-off Delay Time	Inductive Load	–	–	300	ns
Times	Fall Time					
Diode Reverse Recovery Time**	$t_{rr}$	Switching Operation	–	–	150	ns
Diode Reverse Recovery Charge**	$Q_{rr}$	$I_E = 75A$	–	1.4	–	$\mu\text{C}$

### Thermal and Mechanical Characteristics, $T_j = 25^\circ\text{C}$ unless otherwise specified

Characteristics	Symbol	Test Conditions	Min.	Typ.	Max.	Units
Thermal Resistance, Junction to Case	$R_{th(j-c)Q}$	Per IGBT 1/2 Module, $T_C$ Reference Point per Outline Drawing	–		0.43	$^\circ\text{C/W}$
Thermal Resistance, Junction to Case	$R_{th(j-c)D}$	Per FWDi 1/2 Module, $T_C$ Reference Point per Outline Drawing	–	–	0.9	$^\circ\text{C/W}$
Thermal Resistance, Junction to Case	$R_{th(j-c)'Q}$	Per IGBT 1/2 Module, $T_C$ Reference Point Under Chip	–	0.29		$^\circ\text{C/W}$
Contact Thermal Resistance	$R_{th(c-f)}$	Per Module, Thermal Grease Applied	–	0.055	–	$^\circ\text{C/W}$

\*\* Represents characteristics of the anti-parallel, emitter-to-collector free-wheel diode (FWDi).

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